SSF5508

Feathers:

- Advanced trench process technology
- Ultra low Rdson, typical 6mohm
- High avalanche energy, 100% test
- Fully characterized avalanche voltage and current

Description:

The SSF5508 is a new generation of middle voltage and high current N–Channel enhancement mode trench power MOSFET. This new technology increases the device reliability and electrical parameter repeatability. SSF5508 is assembled in high reliability and qualified assembly house.

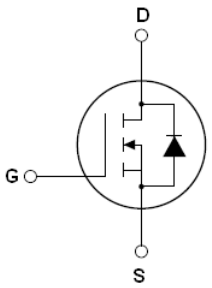
Application:

- Power switching application

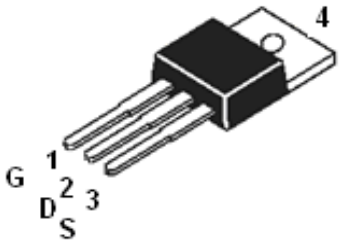
ID =110A

BV=55V

Rdson=4.5 mΩ(typ.)



SSF5508 TOP View (TO220)



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D@T_c=25℃	Continuous drain current,VGS@10V	110	A
I_D@T_c=100℃	Continuous drain current,VGS@10V	80	
I_{DM}	Pulsed drain current ①	400	
P_D@T_C=25℃	Power dissipation	170	W
	Linear derating factor	2.0	W/℃
V_{GS}	Gate-to-Source voltage	±20	V
dv/dt	Peak diode recovery voltage	31	v/ns
E_{AS}	Single pulse avalanche energy ②	480	mJ
E_{AR}	Repetitive avalanche energy	TBD	
T_J T_{STG}	Operating Junction and Storage Temperature Range	–55 to +150	℃

Thermal Resistance

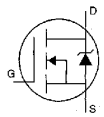
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case	—	0.73	—	℃/W
$R_{\theta JA}$	Junction-to-ambient	—	—	62	

Electrical Characteristics @TJ=25 ℃(unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-to-Source breakdown voltage	55	—	—	V	V_{GS}=0V,I_D=250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	4.5	8	mΩ	V_{GS}=10V,I_D=68A
$V_{GS(th)}$	Gate threshold voltage	2.0		4.0	V	V_{DS}=V_{GS},I_D=250μA
g_{fs}	Forward transconductance	-	58	—	S	V_{DS}=5V,I_D=30A
I_{DSS}	Drain-to-Source leakage current	—	—	2	μA	V_{DS}=55V,V_{GS}=0V
		—	—	10		V_{DS}=55V, V_{GS}=0V,T_J=150℃
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS}=20V

	Gate-to-Source reverse leakage	—	—	-100		V_{GS}=-20V
Q_g	Total gate charge	—	90	—	nC	I_D=30A
Q_{gs}	Gate-to-Source charge	—	14	—		V_{DD}=30V
Q_{gd}	Gate-to-Drain("Miller") charge	—	24	—		V_{GS}=10V
$t_{d(on)}$	Turn-on delay time	—	18.2	—	nS	V_{DD}=30V
t_r	Rise time	—	15.6	—		I_D=2A ,R_L=15Ω
$t_{d(off)}$	Turn-Off delay time	—	70.5	—		R_G=2.5Ω
t_f	Fall time	—	13.8	—		V_{GS}=10V
C_{iss}	Input capacitance	—	3150	—	pF	V_{GS}=0V
C_{oss}	Output capacitance	—	300	—		V_{DS}=25V
C_{rss}	Reverse transfer capacitance	—	240	—		f=1.0MHZ

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	110	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	400		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	T_J=25℃,I_S=68A,V_{GS}=0V ③
t_{rr}	Reverse Recovery Time	—	57	—	nS	T_J=25℃,I_F=68A di/dt=100A/μs ③
Q_{rr}	Reverse Recovery Charge	—	107	—	nC	
t_{on}	Forward Turn-on Time	Intrinsic turn-on time is negligible (turn-on is dominated by Ls + LD)				

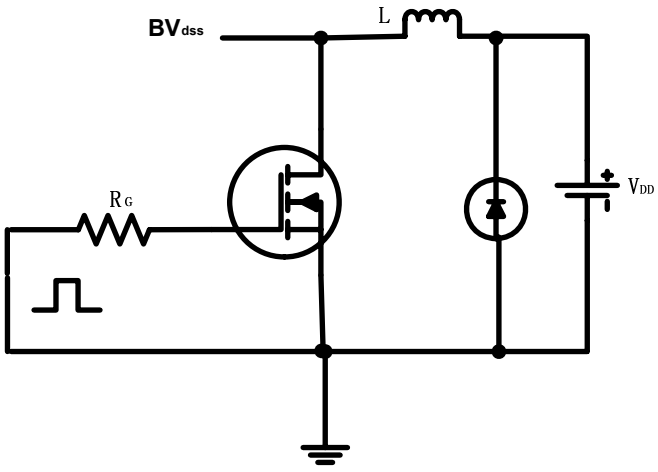
Notes:

① Repetitive rating; pulse width limited by max junction temperature.

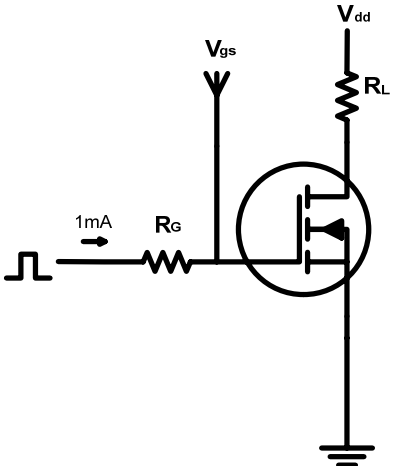
② Test condition: L =0.3mH, ID = 57A, VDD = 27.5V

③ Pulse width≤300μS, duty cycle≤1.5% ; RG = 25Ω Starting TJ = 25°C

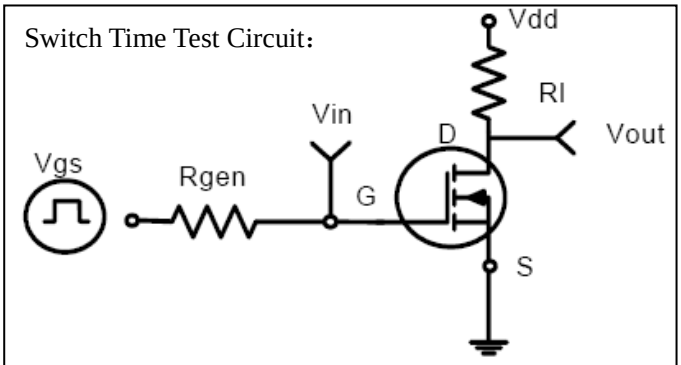
EAS test circuit:



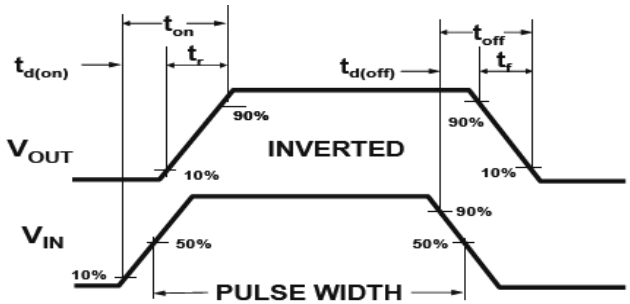
Gate charge test circuit:

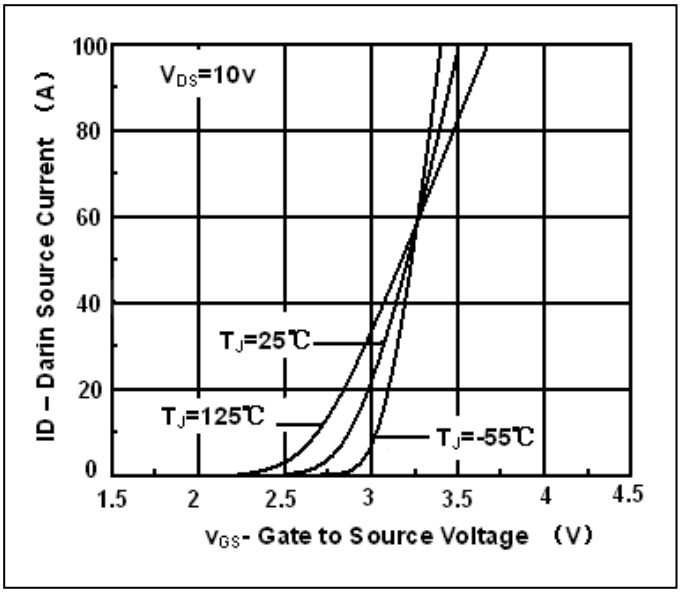


Switch Time Test Circuit:

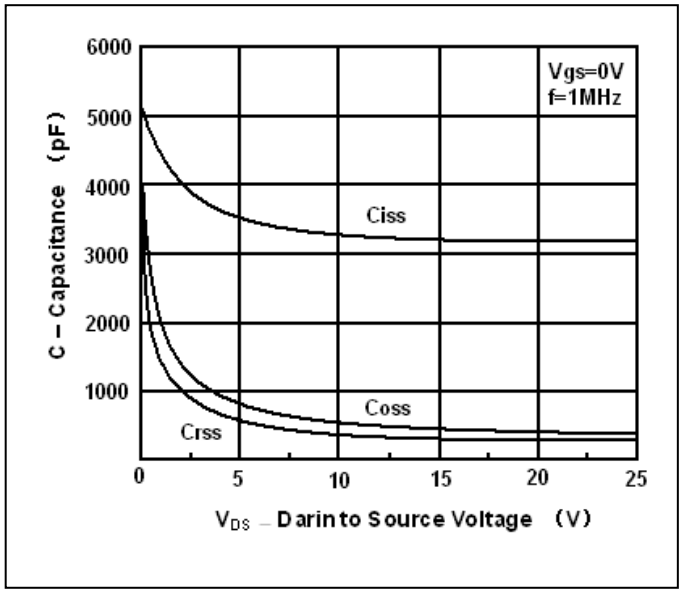


Switch Waveforms:

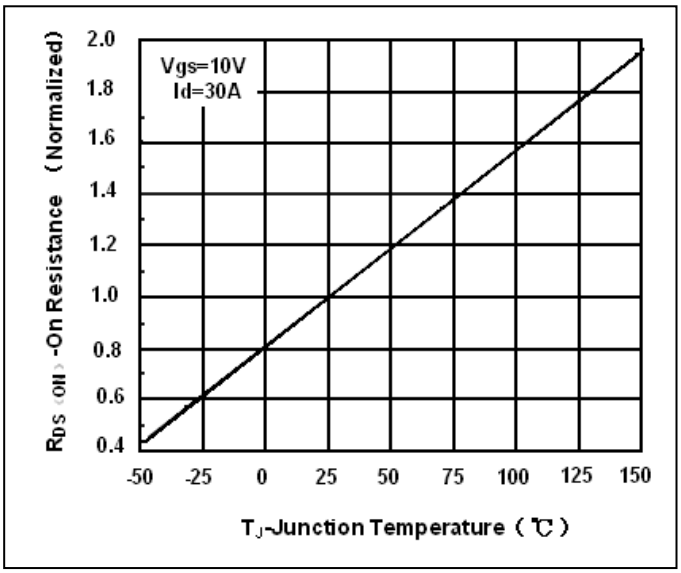




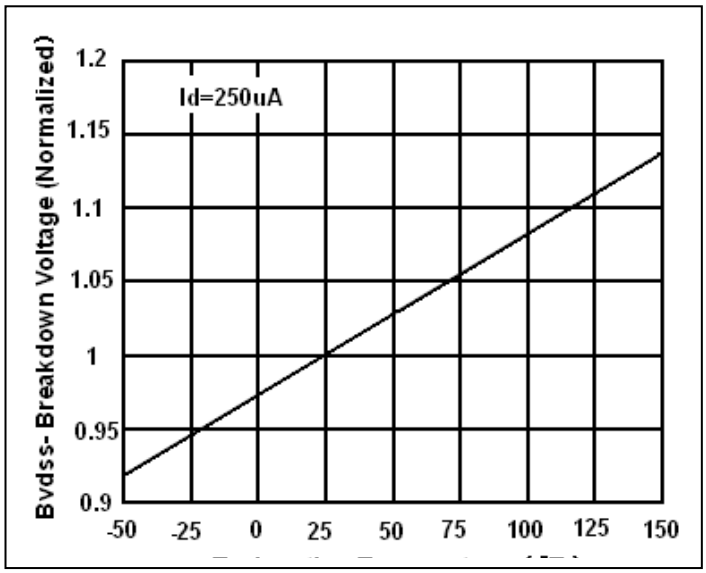
Transfer Characteristic



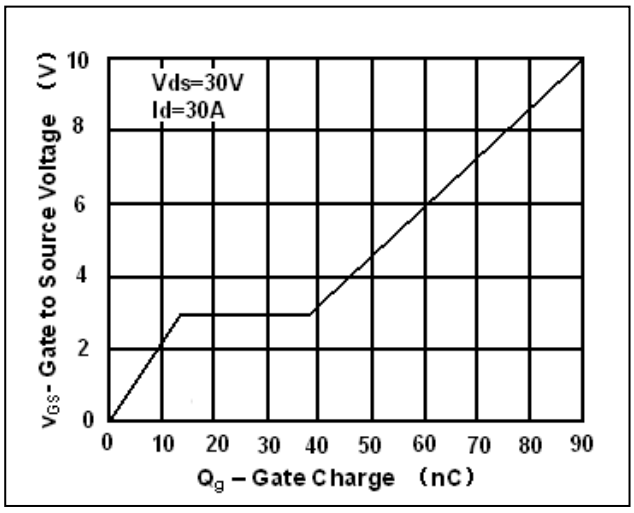
Capacitance



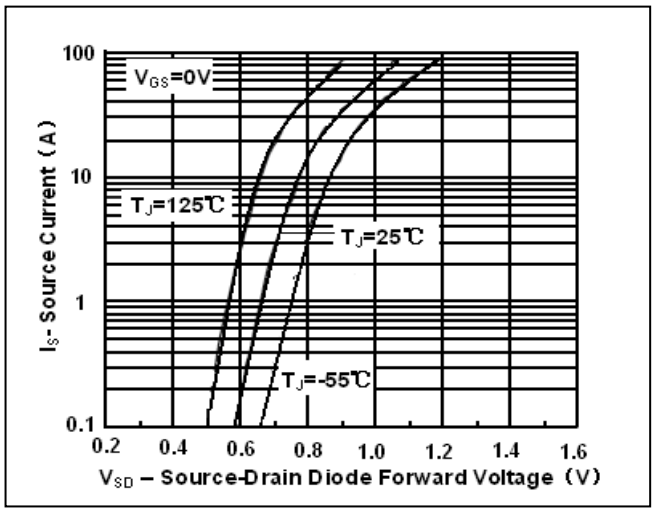
On Resistance vs Junction Temperature



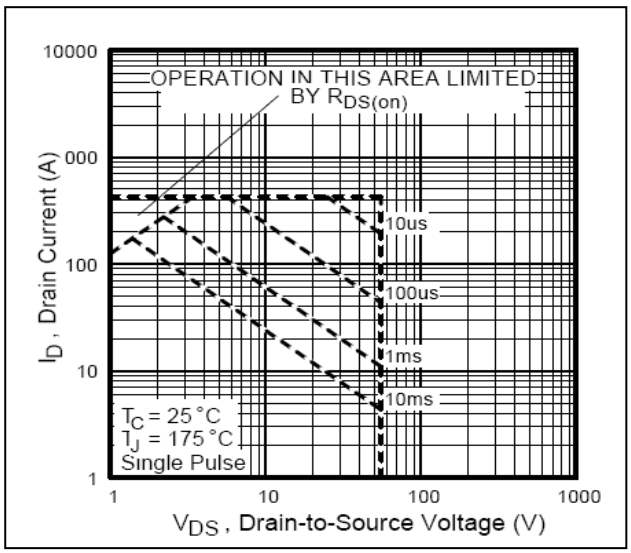
Breakdown Voltage vs Junction Temperature



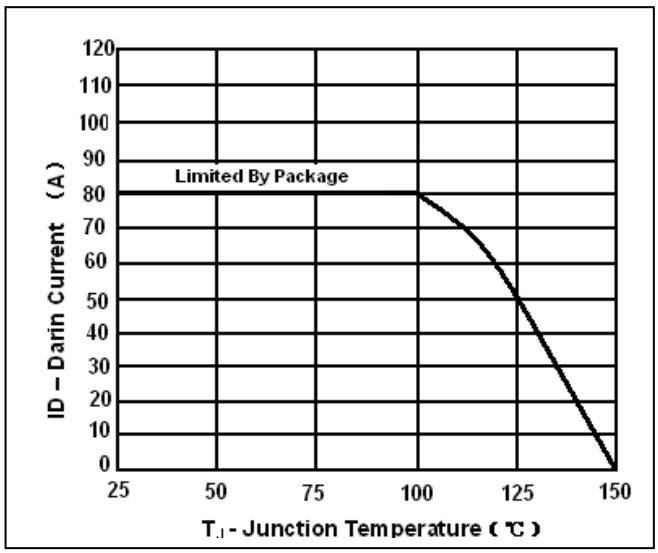
Gate Charge



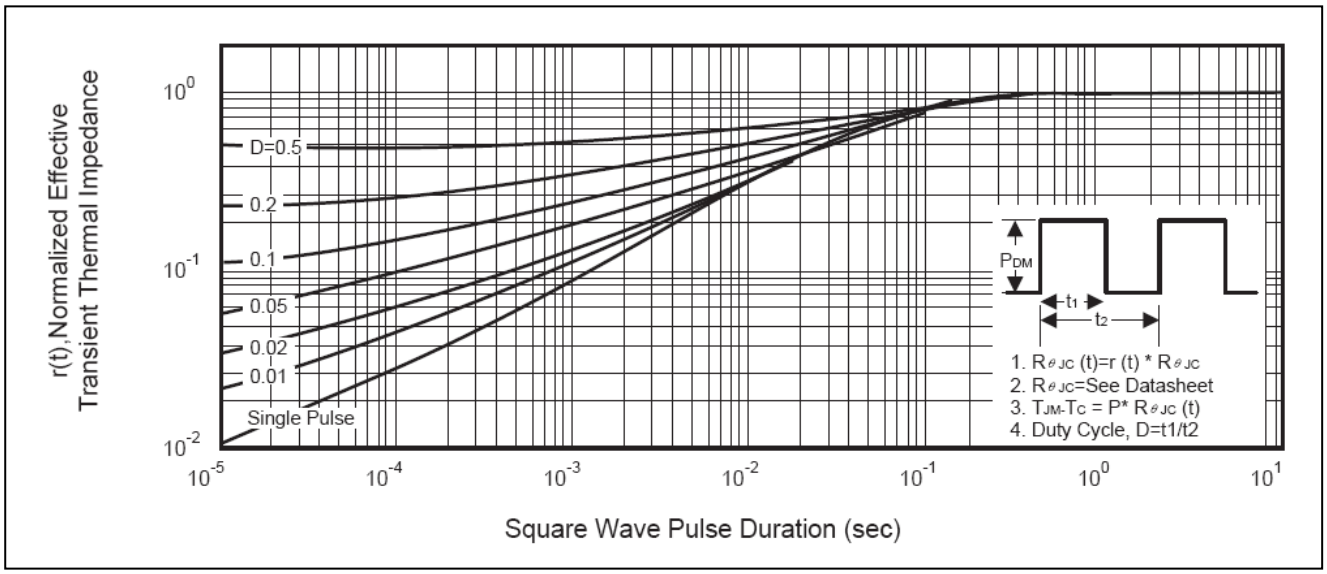
Source-Drain Diode Forward Voltage



Safe Operation Area



Max Drain Current vs Junction Temperature



Transient Thermal Impedance Curve

TO220 MECHANICAL DATA: